

# Variational Solution of the Bhatt-Lee Problem

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We present a large- $N$  variational approach to the Bhatt-Lee problem describing the magnetism of insulating doped semiconductors, based on a disorder-generalization of the resonating-valence-bond theory for quantum antiferromagnets. This method is shown to capture all the qualitative and even quantitative predictions of the strong-disorder renormalization group approach over the entire experimentally relevant energy range. The simplicity of this method allows for an essentially exact analytic solution of the variational problem without any adjustable parameters, by mapping the problem to that of a hard-sphere fluid with an energy (length scale) dependent core diameter.

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The metal-insulator transition (MIT) in doped semiconductors (DS) [1] is one of the most fundamental, yet theoretically less understood problems in condensed matter physics. Even aside from their pivotal technological role, the DS have long been recognized as a bellwether system for the study of quantum criticality at the MIT. Careful transport experiments have revealed sharply defined critical behavior, although with exponents inconsistent with early theoretical predictions [2].

What are the basic physical processes that drive this transition and localize the electrons? Important clues have been provided by the thermodynamic response on the insulating side. Here, no magnetic ordering has been experimentally observed down to the lowest temperatures, while both the spin susceptibility and the specific heat display signatures of randomly interacting localized magnetic moments [1, 3]. This puzzling behavior was largely explained by the Bhatt-Lee (BL) theory [4] of random singlet (RS) formation, using a strong-disorder renormalization group (SDRG) approach [5].

The remarkable success of the BL theory provides strong support to the early ideas of Mott [6], who first emphasized that strong Coulomb repulsion may localize the electrons by converting them into localized magnetic moments. According to this picture, the MIT in DS should be viewed as a disordered version of the Mott transition, a phenomenon dominated by strong correlation effects. An appropriate theory should then be able to describe both the local moment magnetism in the insulator and the transmutation of these local moments into conduction electrons on the metallic side of the MIT. Unfortunately, the SDRG approach of BL, which was so successful in the insulator, is difficult to extend across the transition.

The essential challenge, therefore, is to develop an alternative approach to Mott localization in a strongly disordered situation, one that *at the very least* can reproduce the RS physics of Bhatt and Lee. An attractive avenue to describe strong correlations has emerged in the last twenty years from studies of various Mott sys-

tems, based on resonating-valence bond (RVB) ideas of Anderson [7] and others. At the mean field level, these theories provide variational wavefunctions for quasiparticle states, which become exact in appropriate large- $N$  limits [8]. Very recent work has extended similar variational studies to disordered systems, providing a description of phenomena such as disorder-induced non-Fermi liquid behavior [9], but did not address the physics of inter-site spin correlations central to the BL paradigm.

In this Letter we examine an appropriate  $t$ - $J$  model capable of describing the Mott transition in a disordered environment. While the large- $N$  limit of this model generally reduces to an RVB-like variational problem, here we concentrate on the localized ( $t \rightarrow 0$ ) limit in the presence of strong positional disorder modeling the insulating DS. We show that: (1) the large- $N$  formulation quantitatively reproduces all the key features of the RS regime; (2) an accurate analytic solution of the variational problem can be thus obtained, providing closed form expressions for various physical quantities; and (3) the approach can be directly extended to the metallic side, eliminating the main stumbling block in attacking the MIT in DS.

*Model and large- $N$  formulation.* We start with the large- $N$  formulation of the two-orbital  $t$ - $J$  model,

$$\mathcal{H} = \sum_{\mathbf{k}, \sigma} (\varepsilon_{\mathbf{k}} + \varepsilon_o) c_{\mathbf{k}\sigma}^\dagger c_{\mathbf{k}\sigma} + \sum_{i \neq j, \sigma} t_{ij} \tilde{f}_{i\sigma}^\dagger \tilde{f}_{j\sigma} \quad (1)$$

$$+ \frac{1}{2N} \sum_{i \neq j} J_{ij} \mathbf{S}_i \cdot \mathbf{S}_j + \frac{V}{\sqrt{N}} \sum_{i, \mathbf{k}, \sigma} (e^{i\mathbf{k} \cdot \mathbf{r}_i} c_{\mathbf{k}\sigma}^\dagger \tilde{f}_{i\sigma} + \text{H.c.}),$$

under the constraint of no double occupancy on the  $\tilde{f}$ -orbital. Here each lattice site corresponds to a donor or acceptor which is randomly distributed in a periodic-boundary 3D cube of volume  $V_0 = N_0/\rho_0$ , where  $N_0$  is the number of dopant sites and  $\rho_0$  is the doping concentration. We stay at half-filling for the uncompensated DS,  $\sum_{\mathbf{k}, \sigma} c_{\mathbf{k}\sigma}^\dagger c_{\mathbf{k}\sigma} + \sum_{i\sigma} \tilde{f}_{i\sigma}^\dagger \tilde{f}_{i\sigma} = N_0 N/2$ . The  $c$ -orbital represents the semiconductor conduction band with dispersion  $\varepsilon_{\mathbf{k}}$ , lying at an energy  $\varepsilon_o$  above the hydrogenic  $1s$  impurity bound state (the  $\tilde{f}$ -orbital), and  $V$  is the

hybridization between them.  $\mathbf{S}_i$  is the  $SU(N)$  spin operator of the  $\tilde{f}_i$ -orbital. The hopping between the hydrogenic bound states [10] falls off exponentially with distance  $r_{ij} = |\mathbf{r}_i - \mathbf{r}_j|$ ,  $t_{ij} = t_0 \exp(-r_{ij}/a)$ . Consequently, the antiferromagnetic super-exchange coupling

$$J_{ij} = J_0 \exp(-2r_{ij}/a), \quad (2)$$

where  $J_0 \sim t_0^2$ , and  $a$  is the Bohr radius of the bound state. The projected Hilbert space of the  $\tilde{f}$ -orbital can be treated in the slave-boson formalism  $\tilde{f}_{i\sigma}^\dagger = b_i f_{i\sigma}^\dagger$  enslaved to a constraint on each site  $\sum_\sigma f_{i\sigma}^\dagger f_{i\sigma} + b_i^\dagger b_i = N/2$ .

In this Letter, we focus on the insulating side of the uncompensated DS  $\rho_0 < \rho_c$  ( $\rho_c^{1/3} a \approx 0.25$  for Si:P) where the average inter-site distance  $\Lambda = \rho_0^{-1/3} \gg a$ , which implies that  $t_{ij} \rightarrow 0$ . In this limit, the effective hybridization  $bV$  goes to zero as  $b \rightarrow 0$ , and the electrons become Mott localized on singly-occupied  $\tilde{f}$ -orbitals. This results in an effective Heisenberg Hamiltonian for the insulating uncompensated DS,  $\mathcal{H} = \frac{1}{2N} \sum_{i \neq j} J_{ij} \mathbf{S}_i \cdot \mathbf{S}_j$ . The magnetic behavior of such a disordered Heisenberg system was largely explained by Bhatt and Lee via the SDRG method. Here we investigate the system within the large- $N$  theory [8, 11], which leads to an effective mean-field Hamiltonian through the saddle-point approximation,

$$\mathcal{H} = -\frac{N}{16} \sum_{i \neq j} J_{ij} \left( \Delta_{ij}^* \hat{\Delta}_{ij} + \text{H.c.} - |\Delta_{ij}|^2 \right),$$

with the constraint  $\sum_\sigma f_{i\sigma}^\dagger f_{i\sigma} = N/2$  (of self-conjugate spins) implemented through the local Lagrange multiplier  $\lambda_i$ . Here,  $\hat{\Delta}_{ij} = 2 \sum_\sigma f_{i\sigma}^\dagger f_{j\sigma} / N$  are valence bond (VB) operators and  $\Delta_{ij} = \langle \hat{\Delta}_{ij} \rangle$  are variational parameters which minimize the free energy. They are solved self-consistently at  $N \rightarrow \infty$ , for a given sample realization and temperature. The results are then averaged over many sample realizations.

*Numerical large- $N$  solution.* At any finite temperature, our large- $N$  solution finds two types of spins: localized and VB spins. The localized spins are those isolated from all other ones, *i.e.*,  $\Delta = 0$  for all bonds connecting to them; their contribution to the magnetic susceptibility is simply a Curie term  $\chi_c(T) = \mu_B^2 / k_B T$ . In contrast, each VB spin forms singlet bond ( $\Delta \neq 0$ ) with another spin; their contribution can be neglected at low temperatures. The low- $T$  magnetic susceptibility is, therefore, well approximated by

$$\chi(T) = \rho(T) \chi_c(T), \quad (3)$$

where  $\rho(T)$  is the density of localized/free spins at temperature  $T$ . Fig. 1 shows the normalized magnetic susceptibility  $\chi(T)/\chi(J_0) = J_0 \rho(T) / T \rho_0$  at concentrations  $n = \frac{4\pi}{3} \rho_0 a^3 = 0.004, 0.04, \text{ and } 0.16$  [12]. The susceptibility diverges at low temperatures, consistent with the SDRG results of BL [4]. This divergence is usually fitted by a power law in experiments, but we shall show

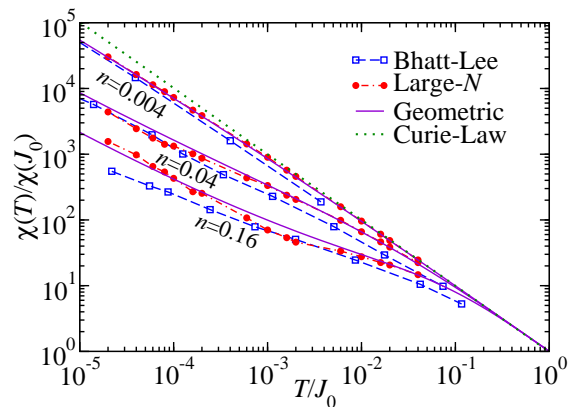


Figure 1: (Color online) Normalized magnetic susceptibility of highly disordered 3D Heisenberg magnets evaluated with the Bhatt-Lee method [4], the large- $N$  self-consistent theory (for systems with  $N_0 = 512$  spins [12]), and the geometric decimation procedure at concentrations  $n = \frac{4\pi}{3} \rho_0 a^3 = 0.004, 0.04, \text{ and } 0.16$ .

later that it should be viewed as a logarithmic correction to the Curie law. The higher the doping concentration, the larger this correction since couplings among spins are stronger. At extremely low concentrations, all spins are essentially free and the magnetic susceptibility follows the Curie law.

*Geometric decimation procedure.* The large- $N$  ground state at zero temperature of such a highly disordered Heisenberg system is essentially a RS state, in which most spins form inert singlets ( $\Delta = 1$ ) with another spin and do *not* correlate with any other spin. To highlight this, we considered a simple four-spin cluster with antiferromagnetic couplings  $J_{ij} > 0$ , and  $J_{23} \gg J_{ij}$  for all  $(i, j) \neq (2, 3)$ . The large- $N$  calculation shows that for  $T > J_{23}$ , all bonds are zero and all four spins are free. As we lower the temperature to  $J_{23}$ , spins  $\mathbf{S}_2$  and  $\mathbf{S}_3$  start to form a VB singlet,  $\Delta_{23} \neq 0$ , and no longer contribute to  $\chi(T)$ . Further reducing the temperature to  $J_{14}$ , spins  $\mathbf{S}_1$  and  $\mathbf{S}_4$  form another VB singlet. There is *no* resonance between the (2,3) and the (1,4) VB singlets. In contrast to the Bhatt-Lee SDRG method, in which there appears a renormalized coupling between  $SU(2)$  spins connected to a strong singlet pair, this effect can be shown to be of order  $1/N$  between  $SU(N)$  spins [13], and thus *drops out* in the large- $N$  limit. While this simplification makes our large- $N$  model amenable to closed form solution, we shall demonstrate that it hardly affects the quantitative predictions of the model within the experimentally relevant temperature range.

This also allows us to state a very simple geometric decimation procedure. We (i) search for the most strongly coupled spin pair, or equivalently, the shortest one [see Eq. (2)], (ii) remove it from the system by coupling the spins in an inert singlet, and (iii) repeat steps (i) and (ii)

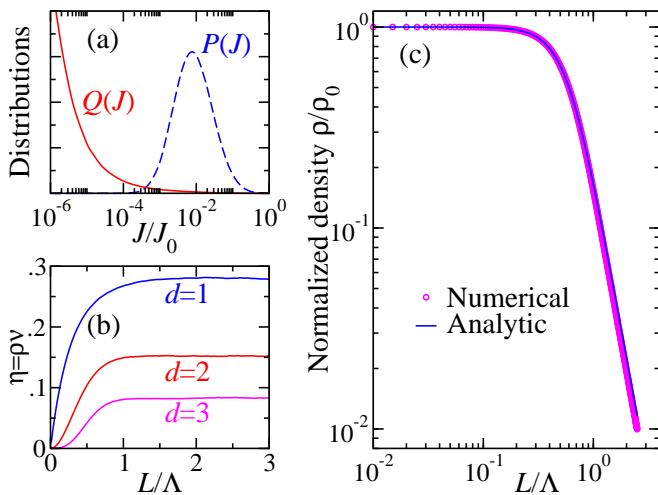


Figure 2: (Color online) (a) The distributions of the nearest neighbor couplings  $P(J)$  and of decimated couplings  $Q(J)$  at concentration  $n = 0.16$ . (b) Numerical results for the packing fraction  $\eta = \rho v$  as a function of decimation length  $L$  for  $d = 1, 2$ , and  $3$ . (c) Comparison between the numerical and analytic [Eq. (5)] results for the free spin density in the geometric decimation procedure for  $d = 3$ . Here, systems with  $N_0 = 4096$  spins averaged over 3000 samples were used [12].

until the desired energy (temperature) scale is reached. We should emphasize that *no* other renormalizations are involved during this decimation procedure. The density of free (undecimated) spins in Eq. (3) is then given by  $\rho(T) = \rho_0 \int_0^T Q(J) dJ$ , where  $Q(J)$  is the distribution of the decimated couplings, shown in Fig. 2(a) for  $n = 0.16$ . The distribution of nearest neighbor couplings,  $P(J)$ , is also plotted for comparison. Note the dramatic difference between  $P(J)$  and  $Q(J)$  which stems from the fact that, during the decimation procedure, longer-distance nearest pairs are *unavoidably* generated. Therefore,  $Q(J)$  will always be singular yielding the divergence of  $\chi(T)$  at low temperatures. As depicted in Fig. 1, this simple geometric decimation procedure captures the essential physics of the large- $N$  theory in describing the magnetic susceptibility of strongly disordered Heisenberg spin systems.

*Analytic solution.* The geometric decimation procedure will give us a long-sought analytic description [14, 15] of the magnetic properties of insulating DS if one can keep track of  $\rho$  as a function of the energy scale  $\Omega = \max\{J_{ij}\}$  (defined as the coupling to be decimated) or, equivalently, the length scale  $L = \min\{r_{ij}\}$  (the distance between the spins in the pair to be decimated). Although the pair approximations [14] considerably simplify the calculations as compared to the SDRG and numerical cluster calculations, they fail to yield an analytic expression for  $\rho$ . On the other hand, the analytic formula proposed by Ponomarev *et al.* involves a tunable parameter [15]. Here we present an accurate analytic solution without any adjustable parameters for a general

$d$ -dimensional system.

Since we remove hierarchically the closest spin pair, we can imagine each spin as a hard sphere of diameter  $L$ , which naturally incorporates the constraint that no spin pair is closer than  $L$  [16]. By removing the spheres that are touching each other, we continuously increase  $L$  until the next closest pair of spins touch each other. The rate equation governing the density of free spins is given by

$$d\rho = -2^d \rho^2 g dv, \quad \text{where } g(\rho) = (1 - \alpha\rho)(1 - \rho v)^{-d} \quad (4)$$

is the radial distribution function [17] of a hard-sphere fluid. Here,  $\alpha$  is a constant which depends only on dimensionality ( $\alpha = 0, 0.436$ , and  $0.5$  for  $d = 1, 2$  and  $3$ , respectively) [17], and  $v$  is the excluded volume of each hard sphere. The negative sign comes from the fact that  $\rho$  decreases as  $L$  increases, and the decrease in  $\rho$  is proportional to the density of available spins  $\rho$  times the probability that two spins (hard spheres) touch each other, *i.e.*,  $2^d \rho g dv$ . The  $2^d$  factor converts the radius of the hard sphere (raised to the power  $d$ ) into its diameter.

The solution of Eq. (4) can be reduced to a quadrature, from which we can deduce that the packing fraction  $\eta = \rho v$  increases monotonically with  $L$ , saturating at large length scales at  $\eta_c$  ( $\simeq 0.333, 0.182$ , and  $0.0968$ , respectively, for  $d = 1, 2$  and  $3$ ). The results of a numerical solution of the decimation procedure are shown in Fig. 2(b), from which we obtain  $\eta_c \simeq 0.2810(5), 0.156(1)$ , and  $0.082(2)$  for  $d = 1, 2$  and  $3$  [18]. Since  $\eta \ll 1$  *throughout* the decimation procedure, our hard sphere liquid remains moderate correlated (away from the strong coupling regime in the vicinity to close packing). This provides a dramatic simplification, since we are now well justified in using the virial expansion  $g^{-1} \approx 1 - (d - \alpha)\rho v$  (this linearized expression is exact [17] in  $d = 1$ ), and find a closed form solution

$$2^d \gamma \rho v = 1 - (\rho/\rho_0)^\gamma, \quad \text{with } \gamma = 1 + (d - \alpha)/2^d, \quad (5)$$

which satisfies the initial condition  $\rho = \rho_0$  at  $v = 0$ . The magnetic susceptibility in Eq. (3) is readily obtained by relating temperature and  $L$  via Eq. (2), *i.e.*,  $2L = a \ln(J_0/T)$ . In the  $L, v \rightarrow \infty$  ( $T \rightarrow 0$ ) limit, the density decays asymptotically as  $\rho \sim v^{-1} \sim L^{-d}$ . Thus the magnetic susceptibility diverges at low temperatures according to

$$\chi(T) \sim \frac{J_0}{T [\ln(J_0/T)]^d}, \quad (6)$$

which can be viewed as a logarithmic correction to the Curie law instead of the power law divergence usually fitted to experiments. The free spin density  $\rho$  extracted from Eq. (5) is plotted in Fig. 2(c) as a function of  $L$ , in excellent agreement with the numerical result of the decimation procedure. Therefore, Eq. (5) provides an accurate analytic solution, without any adjustable parameters, to the large- $N$  theory of the insulating DS.

*Comparison between SDRG and large- $N$ .* It is now natural to ask how reliable the large- $N$  theory is. To address this issue, we compare the well-known RS solution of the 1D random Heisenberg system obtained by the SDRG method [19, 20] with the analytic solution Eq. (5) of the large- $N$  theory. For randomly distributed spins, the length distribution of the nearest neighbor bonds is a Poissonian  $P(L) = \rho_0 \exp(-\rho_0 L)$ , which gives rise to a power-law initial coupling constant distribution

$$P_0(J) = \theta(J)\theta(J_0 - J) \frac{\rho_0 a}{2J_0} \left(\frac{J_0}{J}\right)^{1-\rho_0 a/2}. \quad (7)$$

In this case, the SDRG flow can be followed exactly through all energy scales, yielding [20]

$$\rho' = \rho_0 \left[1 + \frac{\rho_0 a}{2} \ln(J_0/\Omega)\right]^{-2} = \rho_0 (1 + \rho_0 L)^{-2}, \quad (8)$$

where the prime is added to distinguish this SDRG density from the large- $N$  result in Eq. (5). In the asymptotic  $L \rightarrow \infty$  limit,  $\rho' \sim L^{-2}$ , different from the  $L^{-d}$  behavior of the large- $N$  theory as shown in Fig. 3(a). However, upon close inspection, the  $L$  dependences of  $\rho$  and  $\rho'$  [see Fig. 3(b)] reveal that the breakdown occurs only above a length scale  $L^* = 1/\rho_0 = \Lambda$ , corresponding to a breakdown temperature  $T^* = J_0 \exp(-2\Lambda/a)$  below which the renormalized couplings become important in the SDRG procedure. Above  $T^*$ , however, the SDRG theory can be reduced to the simple geometric decimation procedure. The smaller the concentration  $\rho_0$ , the lower  $T^*$  is. In higher dimensions we expect  $T^*$  to be even lower because the renormalization of the lattice connectivity in  $d > 1$  would delay the flow towards the (resonating) random singlet phase [21], if any. Hence, the RG flow should be even closer to the large- $N$  solution. The breakdown temperature at the critical concentration of Si:P is estimated to be  $\lesssim 47$  mK, assuming  $J_0 = 140$  K from Ref. [22]. Remarkably, the temperature window relevant for experiments is above the breakdown temperature, which also explains the success of BL theory.

*Summary and outlook.* We have shown how a variational large- $N$  method provides a physically transparent and quantitatively accurate description of inter-site spin correlations on the insulating side of DS. In the presence of strong positional disorder, each localized spin forms a VB singlet with a rather uniquely defined partner, allowing for a closed-form solution of the problem in the large- $N$  limit. Even more importantly, this approach opens a very attractive avenue to describe the behavior across the MIT by examining the two-orbital  $t$ - $J$  model of Eq. (1) with finite inter-site hopping  $t_{ij}$ . Each  $\tilde{f}$ -spin now has more than one choice: to still form a VB singlet with another localized moment, or to undergo Kondo screening by conduction electrons. Similarly as in the large- $N$  solution of the two-impurity Kondo problem [11], we expect Kondo-screened sites to contribute to the formation of

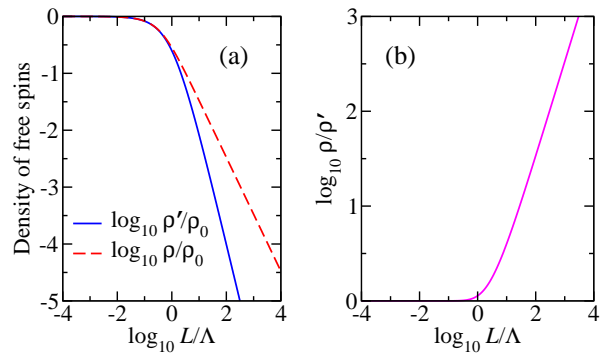


Figure 3: (Color online) Comparisons between the densities of free (undecimated) spins as functions of the length scale  $L$  obtained by the SDRG ( $\rho'$ ) and the large- $N$  ( $\rho$ ) methods, i.e., the geometric solution, in  $d = 1$ .

a coherent Fermi liquid, while VB singlet pairs to “drop out” from the conduction sea and remain Mott localized. Such gradual conversion of the correlated electron fluid into a localized VB solid may provide a microscopic underpinning for the phenomenological “two-fluid” model [3] - possibly the key missing link for cracking the metal-insulator transition in doped semiconductors.

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